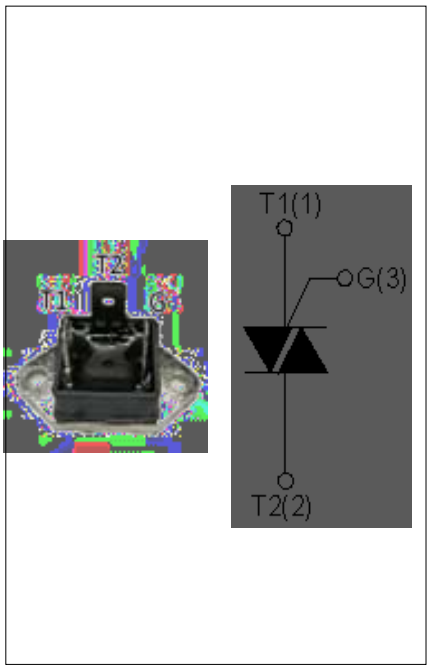
JST55 Series 55A TRIACs

Rev.4.2 July 12 2021

DESCRIPTION:

JST55 series triacs, with high ability to withstand the shock



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	55	A
V_{ISO}	2500	V
V_{DRM} /V_{RRM}	600 and 800 and 1200 and 1600	V

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage (T_j=25)	V_{DRM}	600 /800/1200/1600	V
Repetitive peak reverse voltage (T_j=25)	V_{RRM}	600 /800/1200/1600	V

		V_{RRM} +100	V
RMS on-state current	TG-C (T_C=90)	$I_{T(RMS)}$	55	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	550	A
I^2t value for fusing (t_P=10ms)		I^2t	1500	A^2s
Critical rate of rise of on-state current (I_G =2×I_{GT})		dI/dt	100	A/μs
Peak gate current		I_{GM}	8	A
Average gate power dissipation		$P_{G(AV)}$	2	W
Peak gate power		P_{GM}	10	W
Insulation voltage(A.C,F=50Hz,1min)		V_{ISO}	2500	V

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX	50	mA
V_{GT}		- -	MAX	1.3	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3KΩ	- -	MIN	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX	80	mA
				100	
I_H	I_T =100mA		MAX	60	mA

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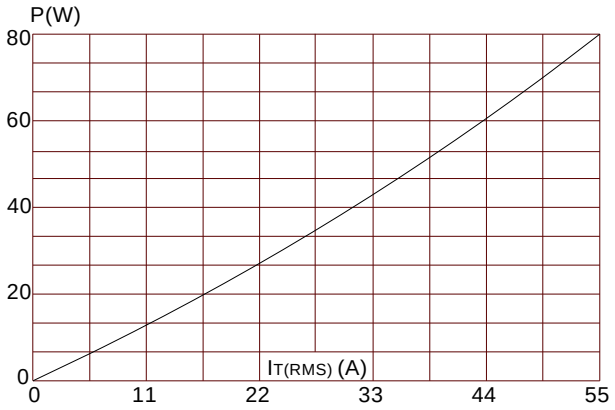
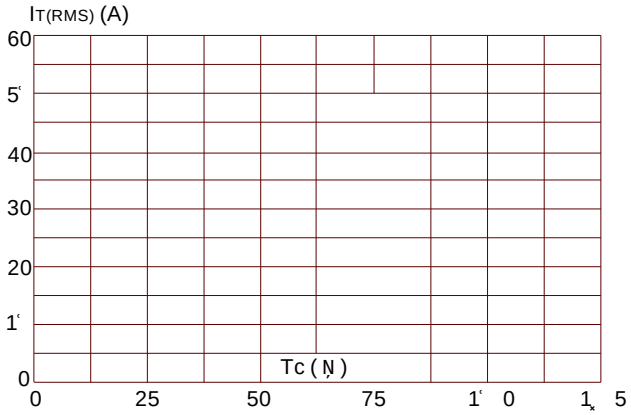
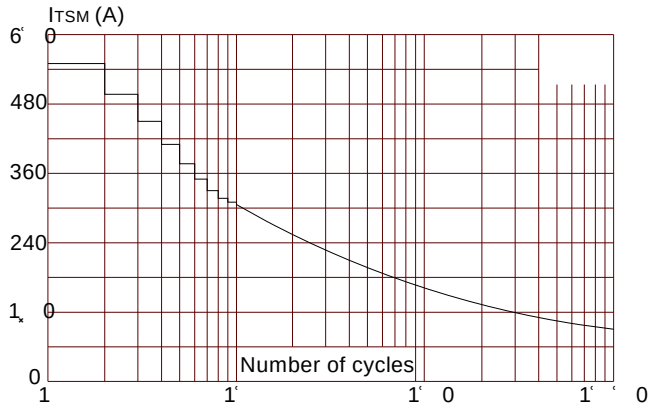
Ph G.1 Maximum po ˝ er dissipation versus RMS O x -state current



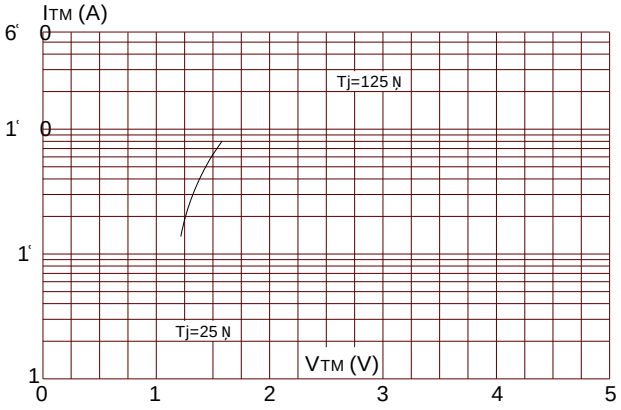
Ph G.2 RMS on- tate current versus case temperature



Ph G.3 Sur ` E peak o x -state current versus Number of cycles



Ph G.4 On-state characteristics (maximum values)



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